Product data sheet

1. Product profile

1.1 General description

Ultrafast epitaxial rectifier diode in a SOD113 (TO-220F) plastic package.

1.2 Features

- Fast switching
- Soft recovery characteristic
- Low forward voltage drop
- Low thermal resistance
- Isolated package

1.3 Applications

- High frequency switched-mode power supplies
- Discontinuous Current Mode (DCM)Power Factor Correction (PFC)

1.4 Quick reference data

- V_{RRM} ≤ 600 V
- V_F ≤ 1.11 V

- $I_{F(AV)} \le 5 A$
- $t_{rr} \le 60 \text{ ns}$

2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	cathode (k)		
2	anode (a)	mb	k — ├ a <i>001aaa020</i>
mb	mounting base; isolated		
		SOD113 (2-lead TO-220	OF)



3. Ordering information

Table 2. Ordering information

Type number	Package		
	Name	Description	Version
BYV25X-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 'full pack'	SOD113

4. Limiting values

Table 3. Limiting values

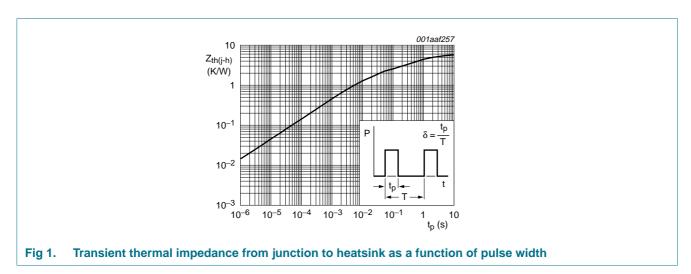
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	square waveform; δ = 1.0; $T_h \le 100$ °C	-	600	V
I _{F(AV)}	average forward current	square waveform; δ = 0.5; $T_h \le$ 115 °C	-	5	Α
I _{FRM}	repetitive peak forward current	square waveform; δ = 0.5; $T_h \le$ 115 °C	-	10	Α
I _{FSM}	non-repetitive peak forward	t = 10 ms; sinusoidal waveform	-	60	Α
	current	t = 8.3 ms; sinusoidal waveform	-	66	Α
T _{stg}	storage temperature		-40	+150	°C
T _i	junction temperature		-	150	°C

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; see Figure 1	-	-	5.5	K/W
		without heatsink compound	-	-	5.9	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W



6. Isolation characteristics

Table 5. Isolation limiting values and characteristics

 $T_h = 25 \,^{\circ}C$ unless otherwise specified.

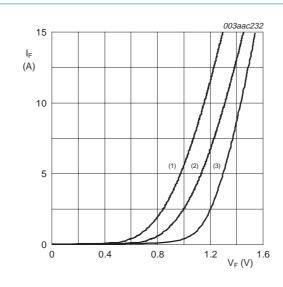
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	from all terminals to external heatsink; $f = 50 \text{ Hz}$ to 60 Hz; sinusoidal waveform; relative humidity $\leq 65 \%$; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink; f = 1 MHz	-	10	-	pF

7. Characteristics

Table 6. Characteristics

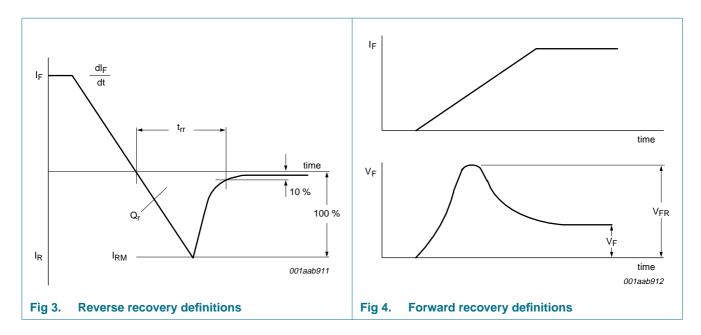
 $T_i = 25 \,^{\circ}C$ unless otherwise specified

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _F	forward voltage	$I_F = 5 \text{ A}$; $T_j = 150 ^{\circ}\text{C}$; see Figure 2	-	0.97	1.11	V
		I _F = 5 A	-	1.12	1.30	V
I _R	reverse current	V _R = 600 V	-	2	50	μΑ
		$V_R = 600 \text{ V}; T_j = 100 ^{\circ}\text{C}$	-	0.1	0.35	mA
Dynamic o	haracteristics					
Q _r	recovered charge	I_F = 2 A to V_R \geq 30 V; dI_F/dt = 20 A/ μ s; see Figure 3	-	40	70	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A to V}_R \ge 30 \text{ V};$ $dI_F/dt = 100 \text{ A/}\mu\text{s}; \text{ see } \underline{\text{Figure 3}}$	-	50	60	ns
I _{RM}	peak reverse recovery current	I_F = 10 A to V_R \geq 30 V; dI_F/dt = 50 A/ μ s; T_j = 100 °C; see Figure 3	-	3	5.5	Α
V_{FR}	forward recovery voltage	$I_F = 10 \text{ A}$; $dI_F/dt = 10 \text{ A/}\mu\text{s}$; see Figure 4	-	3.2	-	V



- (1) $T_j = 150 \,^{\circ}\text{C}$; typical values
- (2) $T_j = 150 \,^{\circ}\text{C}$; maximum values
- (3) $T_j = 25$ °C; maximum values

Fig 2. Forward current as a function of forward voltage



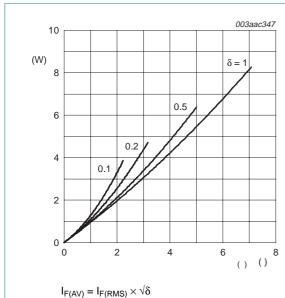


Fig 5. Forward power dissipation as a function of average forward current; square waveform; maximum values

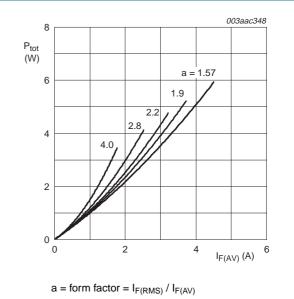
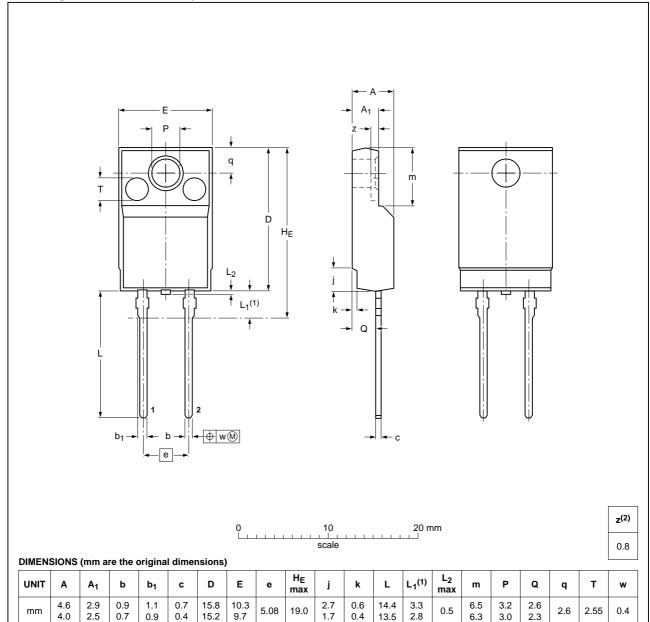


Fig 6. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

8. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 'full pack'

SOD113



Notes

- 1. Terminals are uncontrolled within zone L₁.
- 2. z is depth of T.

OUTLINE VERSION		REFER	ENCES	EUROPEAN	ISSUE DATE
	IEC	JEDEC	JEITA	PROJECTION	1330E DATE
SOD113		2-lead TO-220F			02-04-09 07-06-18

Fig 7. Package outline SOD113 (2-lead TO-220F)

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9. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYV25X-600_1	20080812	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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